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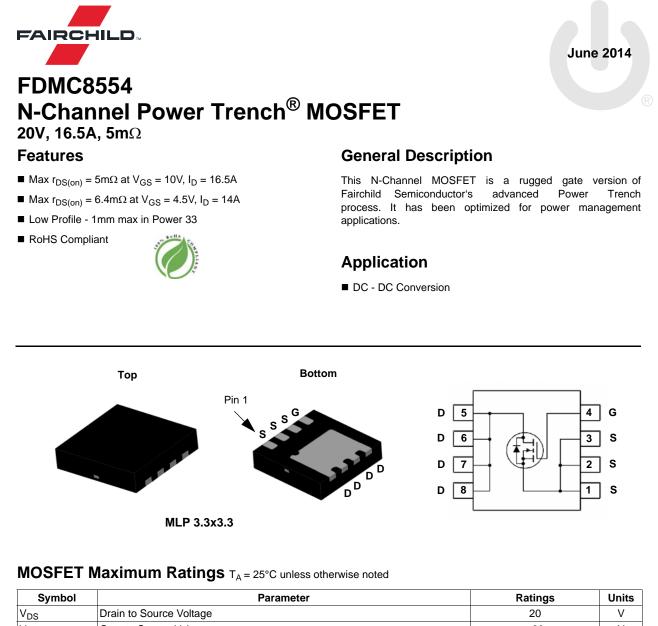


ON Semiconductor®

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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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Symbol	Parameter			Ratings	Units	
V _{DS}	Drain to Source Voltage			20	V	
V _{GS}	Gate to Source Voltage			±20	V	
	Drain Current -Continuous	$T_{C} = 25^{\circ}C$		16.5		
I _D	-Continuous	$T_A = 25^{\circ}C$	(Note 1a)	16.5	А	
	-Pulsed			36		
Р	Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$		41	W	
P _D	Power Dissipation	$T_A = 25^{\circ}C$	(Note 1a)	2.0	vv	
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C	

Thermal Characteristics

R_{\thetaJC}	Thermal Resistance, Junction to Case	3	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	C/vv

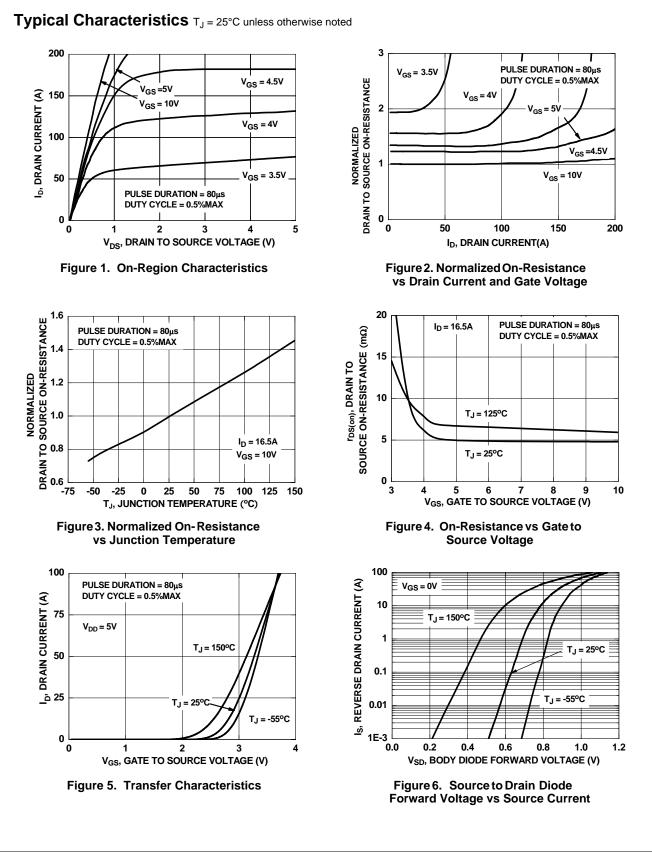
Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
FDMC8554	FDMC8554	Power 33	wer 33 7" 8mm		3000 units	

FDMC8554 N-Channel PowerTrench[®] MOSFET

FDMC8554
N-Channel
PowerTrench [®]
MOSFET

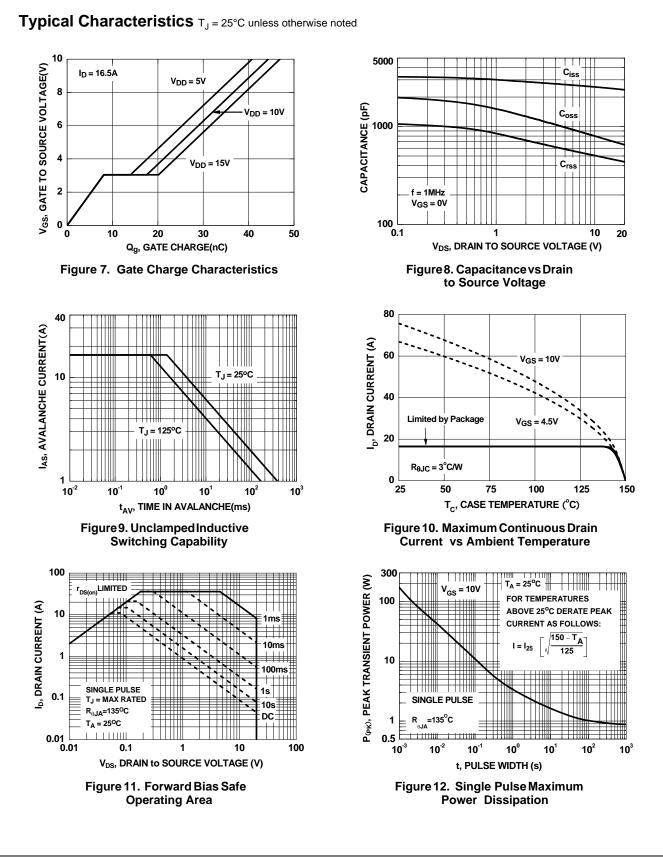
Parameter	Test Conditions	Min	Тур	Max	Units
acteristics					
Drain to Source Breakdown Voltage	$I_{D} = 250 \mu A, V_{GS} = 0 V$	20			V
Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to 25°C		15.7		mV/°C
Zero Gate Voltage Drain Current	$V_{DS} = 16V,$ $V_{CS} = 0V$ $T_{1} = 125^{\circ}C$			1 100	μA
Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
			•	•	1
	$V_{00} = V_{00}$ $I_0 = 250 \mu A$	1.0	18	3.0	V
-		1.0		5.0	
Temperature Coefficient	$I_D = 250\mu A$, referenced to 25°C		-6.1		mV/°0
	V _{GS} = 10V, I _D = 16.5A		3.6	5.0	
Drain to Source On Resistance	$V_{GS} = 4.5V, I_{D} = 14A$		4.6	6.4	mΩ
	$V_{GS} = 10V, I_D = 16.5A, T_J = 125^{\circ}C$		5.4	7.1	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 16.5A$		62		S
Characteristics					
			2540	3380	pF
	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V},$		795	1060	pF
	f = 1MHz		510	765	pF
Gate Resistance	f = 1MHz		1.2		Ω
Turn-On Delay Time Rise Time Turn-Off Delay Time	V_{DD} = 10V, I _D = 16.5A V_{GS} = 10V, R _{GEN} = 6Ω		13 10 32	24 20 51	ns ns ns
Fall Time			7	14	ns
Total Gate Charge at 10V			44	62	nC
Total Gate Charge at 4.5V	V _{DD} = 10V, I _D = 16.5A		24	34	nC
Gate to Source Gate Charge			8.5		nC
Gate to Drain "Miller" Charge			10		nC
urce Diode Characteristics					
Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_{S} = 16.5A$ (Note 2)		0.8	1.3	V
Reverse Recovery Time			31	47	ns
Reverse Recovery Charge	$F = 10.5A$, $d/dt = 100A/\mu s$		22	33	nC
Reverse Recovery Charge mined with the device mounted on a 1in ² pad 2 oz copper pa ard design.	ed on b. 13	5°C/W wh	22	33 nile R _{0CA} is d on a	n
a 1 in ² pad of 2 oz coppe	Ĩ				
	acteristics Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate to Source Leakage Current acteristics Gate to Source Threshold Voltage Gate to Source Threshold Voltage Gate to Source Threshold Voltage Temperature Coefficient Drain to Source On Resistance Forward Transconductance Characteristics Input Capacitance Output Capacitance Gate Resistance g Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge at 10V Total Gate Charge at 4.5V Gate to Source Gate Charge Gate to Drain "Miller" Charge urce Diode Characteristics Source to Drain Diode Forward Voltage Reverse Recovery Time Reverse Recovery Time Reverse Recovery Time	acteristics Drain to Source Breakdown Voltage I _D = 250µA, V _{GS} = 0V Breakdown Voltage Temperature I _D = 250µA, referenced to 25°C Coefficient V _{DS} = 16V, V _{GS} = 0V Zero Gate Voltage Drain Current V _{DS} = 16V, V _{GS} = 0V Gate to Source Leakage Current V _{GS} = ±20V, V _{DS} = 0V acteristics Gate to Source Threshold Voltage I _D = 250µA, referenced to 25°C Gate to Source Threshold Voltage I _D = 250µA, referenced to 25°C Temperature Coefficient I _D = 250µA, referenced to 25°C Drain to Source On Resistance V _{GS} = 10V, I _D = 16.5A Drain to Source On Resistance V _{GS} = 10V, I _D = 16.5A Input Capacitance V _{DS} = 5V, I _D = 10V, V _{GS} = 0V, f = 10HZ Qutput Capacitance f = 1MHz Gate Resistance f = 1MHz g Characteristics Turn-On Delay Time Turn-Off Delay Time V _{DD} = 10V, I _D = 16.5A Fall Time Total Gate Charge at 10V Total Gate Charge at 4.5V Q _{GS} = 0V, I _S = 10V, I _D = 16.5A Gate to Drain "Miller" Charge V _{DD} = 10V, I _D = 16.5A urce Diode Characteristics Gate to Drain Time" Total Gate Charge at 4.5V Q _S = 0V, I _S = 16.5A (Note 2)	acteristics Drain to Source Breakdown Voltage I _D = 250µA, V _{GS} = 0V 20 Breakdown Voltage Temperature I _D = 250µA, referenced to 25°C 20 Zero Gate Voltage Drain Current V _{DS} = 16V, V _{GS} = 0V T _J = 125°C Gate to Source Leakage Current V _{GS} = ±20V, V _{DS} = 0V 0 acteristics Gate to Source Threshold Voltage V _{GS} = ±20V, V _{DS} = 0V 1.0 Gate to Source Threshold Voltage V _{GS} = ±20V, V _{DS} = 0V 1.0 Gate to Source Threshold Voltage V _{GS} = ±20V, V _{DS} = 0V 1.0 Gate to Source Threshold Voltage V _{GS} = ±20V, V _{DS} = 0V, I _D = 16.5A 1.0 Drain to Source On Resistance V _{GS} = 10V, I _D = 16.5A, V _{DS} = 10V, I _D = 16.5A 1.0 Drain to Source On Resistance V _{DS} = 10V, V _{GS} = 0V, f = 10HA 1.0 Reverse Transfer Capacitance V _{DS} = 10V, V _{GS} = 0V, f = 11HA 1.0 Gate Resistance f = 1MHz 1.0 1.0 Gate Charge at 10V Tum-On Delay Time V _{DS} = 10V, I _D = 16.5A 1.0 Turm-Off Delay Time V _{DD} = 10V, I _D = 16.5A 1.0 1.0 Gate to Source Gate Charge 10V 100 1.0 1.0	acteristicsDrain to Source Breakdown Voltage $I_D = 250\mu$ A, $V_{GS} = 0V$ 20Breakdown Voltage Temperature Coefficient $I_D = 250\mu$ A, referenced to 25° C15.7Zero Gate Voltage Drain Current $V_{DS} = 16V$, $V_{GS} = 20V$ $T_J = 125^{\circ}$ C15.7Gate to Source Leakage Current $V_{GS} = V_{DS}$. $I_D = 250\mu$ A1.01.8Gate to Source Threshold Voltage $I_D = 250\mu$ A, referenced to 25° C-6.1Gate to Source Threshold Voltage $I_D = 250\mu$ A, referenced to 25° C-6.1Temperature Coefficient $I_D = 250\mu$ A, referenced to 25° C-6.1Drain to Source On Resistance $V_{GS} = 10V$, $I_D = 16.5A$ 3.6V_{GS} = 10V, $I_D = 16.5A$, $T_J = 125^{\circ}$ C5.4Forward Transconductance $V_{DS} = 5V$, $I_D = 16.5A$ 62CharacteristicsInput Capacitance $V_{DS} = 10V$, $V_{GS} = 0V$, $I_T = 125^{\circ}$ C5.4Input Capacitance $V_{DS} = 10V$, $V_{CS} = 0V$, $I_T = 125^{\circ}$ C5.4Geare Resistance $f = 1MHz$ 1.212g CharacteristicsInput Capacitance I_T 1.2Turn-On Delay Time $V_{CS} = 10V$, $I_D = 16.5A$ 10Turn-Of Delay Time $V_{CS} = 10V$, $R_{GEN} = 6\Omega$ 3.2Fall Time77103.2Fall Time7104.4Total Gate Charge at $10V$ $V_{CS} = 0V$, $I_S = 16.5A$ 10Gate to Source Gate Charge8.53.53.4Gate to Drain Diode Forward Voltage $V_{GS} = 0V$, $I_S = 16.5A$ <	acteristicsDrain to Source Breakdown Voltage $I_D = 250\mu$ A, $V_{GS} = 0V$ 20Breakdown Voltage Temperature $I_D = 250\mu$ A, referenced to 25°C15.7Zero Gate Voltage Drain Current $V_{DS} = 16V$, $V_{GS} = 0V$ 1Zero Gate Voltage Drain Current $V_{DS} = 16V$, $V_{GS} = 0V$ 1Gate to Source Leakage Current $V_{GS} = 20V$, $V_{DS} = 0V$ ±100acteristicsGate to Source Threshold Voltage $V_{GS} = V_{DS}$, $I_D = 250\mu$ A1.01.8Temperature Coefficient $I_D = 250\mu$ A, referenced to 25°C-6.1Drain to Source On Resistance $V_{GS} = 10V$, $I_D = 16.5A$ 3.65.0V_{GS} = 10V, $I_D = 16.5A$, $I_J = 125^{\circ}C$ 5.47.1Forward Transconductance $V_{DS} = 5V$, $I_D = 16.5A$ 62CharacteristicsInput Capacitance $V_{DS} = 10V$, $V_{GS} = 0V$, $I_D = 16.5A795Output CapacitanceI = 1MHz1.2g CharacteristicsTurn-On Delay TimeFall TimeV_{CS} = 10V, I_D = 16.5A10Turn-On Delay TimeFall TimeV_{CS} = 10V, I_D = 16.5A10Total Gate Charge at 4.5VV_{DD} = 10V, I_D = 16.5A10Gate to Source Gate ChargeGate to Drain "Miller" Charge10urce Diode Characteristics1010Source to Drain Diode Forward VoltageV_{GS} = 0V, I_S = 16.5A0.8Turn-On Delay TimeFall Time1010Urce Diode Characteristics1010$



FDMC8554 Rev.C2

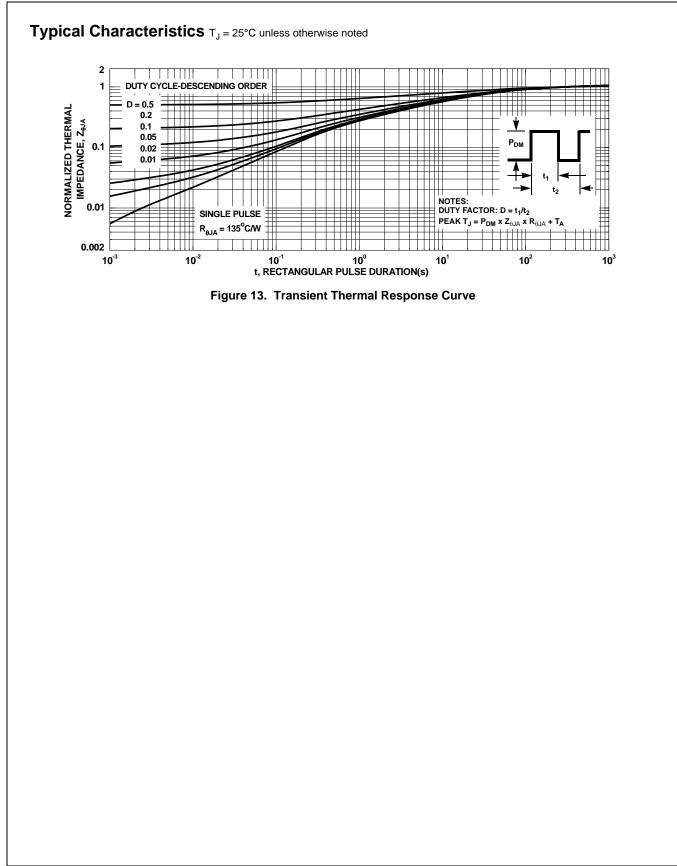
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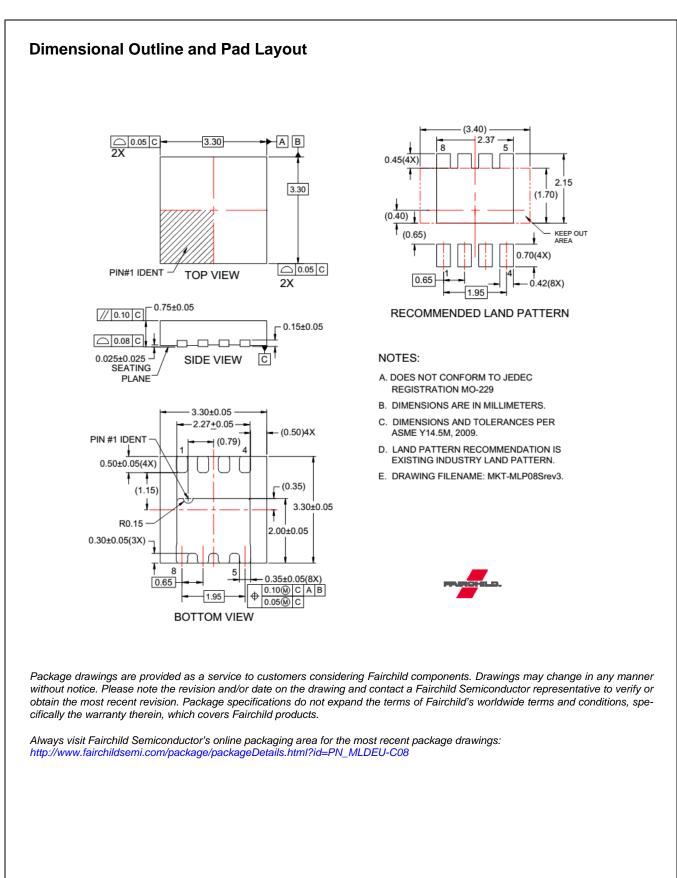


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Definition of Terms

Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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